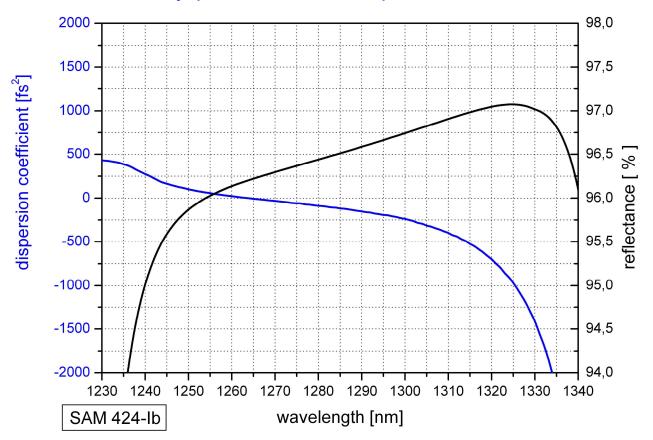


SAM[™] Data Sheet SAM-1300-4-10ps-x, λ = 1300 nm

Laser wavelength		$\lambda = 1300 \text{ nm}$
High reflection band		λ = 1240 1340 nm
Saturable absorptance		$A_0 = 4 \%$
Saturation fluence		Φ_{sat} = 70 µJ/cm ²
Relaxation time constant		$\tau \leq 10 \text{ ps}$
Modulation depth		∆R = 2.5 %
Damage threshold		$\Phi = 3 \text{ mJ/cm}^2$
Chip area		4.0 mm x 4.0 mm; other dimensions on request
Chip thickness		450 μm
Protection		the SAM is protected with a dielectric front layer
Mounting option \mathbf{x} denotes the type of mounting as follows: $\mathbf{x} = 0$ unmounted		
x = 2	12.7 g 25.4 g	glued on a gold plated Cu-cylinder with 12.7 mm \emptyset glued on a gold plated Cu-cylinder with 25.4 mm \emptyset
X = 1	12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm \emptyset

•	
x = 12.7 s	soldered on a gold plated Cu-cylinder with 12.7 mm $arnothing$
x = 25.4 s	soldered on a gold plated Cu-cylinder with 25.4 mm $arnothing$
x = 25.0 w	soldered on a water cooled Cu-cylinder with 25.0 mm $arnothing$
x = FC	mounted on a 1 m monomode fiber cable with FC connector

Low intensity spectral reflectance and dispersion coefficient D₂





Group Delay Dispersion (GDD)

Dispersion coefficient
$$D_2(\omega) = \frac{\partial^2 \varphi}{\partial \omega^2}$$
 with φ - reflected phase
 $\omega = 2\pi \frac{c}{\lambda}$ - angular frequency